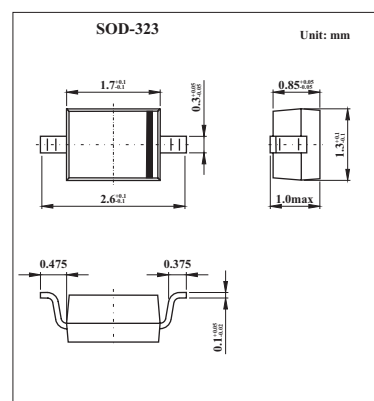


Silicon PIN Diode

BAR 63-03W

■ Features

- PIN diode for high speed switching of RF signals
- Low forward resistance
- Very low capacitance
- For frequencies up to 3 GHz



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	50	V
Forward current	I _F	100	mA
Total Power dissipation T _s ≤ 111°C	P _{tot}	250	mW
Operating temperature range	T _{op}	-55 to +150	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Junction - soldering point ¹⁾	R _{thJA}	≤ 235	K/W
Junction-soldering point	R _{thJS}	≤ 155	K/W

Note:

1.Package mounted on alumina 15mm x 16.7mm x 0.7mm

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V _(BR)	I _R = 5 μA	50			V
Reverse current	I _R	V _R = 50 V			50	nA
Forward voltage	V _F	I _F = 100 mA		0.95	1.2	V
Diode capacitance	C _T	V _R = 0 V, f = 100 MHz		0.3		pF
		V _R = 5 V, f = 1 MHz		0.21	0.3	
Forward resistance	r _f	I _F = 5 mA, f = 100 MHz		1.2	2	Ω
		I _F = 10 mA, f = 100 MHz		1		
Charge carrier life time	τ _{rr}	I _F = 10 mA, I _R = 6 mA, I _R = 3mA		75		ns
Series inductance	L _s			2		nH

■ Marking

Marking	G
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